



# PHM15NQ20T

TrenchMOS™ standard level FET

Rev. 03 — 11 September 2003

Product data

## 1. Product profile

### 1.1 Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

### 1.2 Features

- SOT96 (SO-8) footprint compatible
- Surface mounted package
- Low thermal resistance
- Low profile.

### 1.3 Applications

- DC-to-DC primary side
- Portable appliances.

### 1.4 Quick reference data

- $V_{DS} \leq 200 \text{ V}$
- $P_{tot} \leq 62.5 \text{ W}$
- $I_D \leq 17.5 \text{ A}$
- $R_{DSon} \leq 80 \text{ m}\Omega$ .

## 2. Pinning information

Table 1: Pinning - SOT685-1 (QLPAK), simplified outline and symbol

| Pin     | Description                           | Simplified outline        | Symbol        |
|---------|---------------------------------------|---------------------------|---------------|
| 1,2,3   | source (s)                            | <p>Bottom view MBL585</p> | <p>MBB076</p> |
| 4       | gate (g)                              |                           |               |
| 5,6,7,8 | drain (d)                             |                           |               |
| mb      | mounting base, connected to drain (d) |                           |               |

**SOT685-1 (QLPAK)**

[1] Shaded area indicates pin 1 identifier.

### 3. Ordering information

**Table 2: Ordering information**

| Type number | Package |                                                         | Version |
|-------------|---------|---------------------------------------------------------|---------|
|             | Name    | Description                                             |         |
| PHM15NQ20T  | QLPAK   | Plastic surface mounted package; no leads; 8 terminals. | SOT685  |

### 4. Limiting values

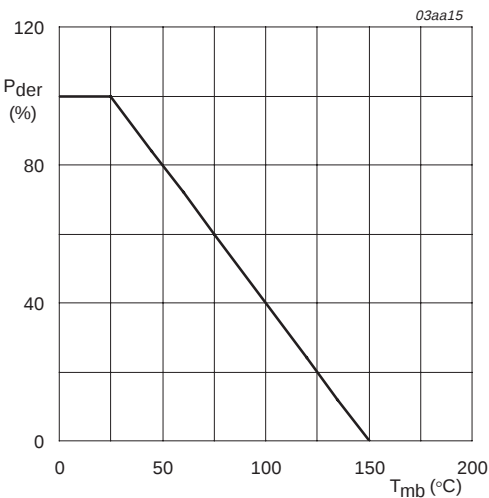
**Table 3: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                      | Parameter                                    | Conditions                                                                                                                                                                                 | Min                                | Max      | Unit |
|-----------------------------|----------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------|----------|------|
| $V_{DS}$                    | drain-source voltage (DC)                    | $25\text{ °C} \leq T_j \leq 150\text{ °C}$                                                                                                                                                 | -                                  | 200      | V    |
| $V_{DGR}$                   | drain-gate voltage (DC)                      | $25\text{ °C} \leq T_j \leq 150\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$                                                                                                                  | -                                  | 200      | V    |
| $V_{GS}$                    | gate-source voltage (DC)                     |                                                                                                                                                                                            | -                                  | $\pm 20$ | V    |
| $I_D$                       | drain current (DC)                           | $T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <b>Figure 2 and 3</b>                                                                                                                   | -                                  | 17.5     | A    |
|                             |                                              | $T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <b>Figure 2</b>                                                                                                                        | -                                  | 11       | A    |
| $I_{DM}$                    | peak drain current                           | $T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <b>Figure 3</b>                                                                                                       | -                                  | 60       | A    |
| $P_{tot}$                   | total power dissipation                      | $T_{mb} = 25\text{ °C}$                                                                                                                                                                    | -                                  | 62.5     | W    |
| $T_{stg}$                   | storage temperature                          |                                                                                                                                                                                            | -55                                | +150     | °C   |
| $T_j$                       | junction temperature                         |                                                                                                                                                                                            | -55                                | +150     | °C   |
| <b>Source-drain diode</b>   |                                              |                                                                                                                                                                                            |                                    |          |      |
| $I_S$                       | source (diode forward) current (DC)          | $T_{mb} = 25\text{ °C}$                                                                                                                                                                    | -                                  | 17.5     | A    |
| $I_{SM}$                    | peak source (diode forward) current          | $T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$                                                                                                                         | -                                  | 60       | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                                                            |                                    |          |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | unclamped inductive load; $I_D = 11\text{ A}$ ; $t_p = 0.14\text{ ms}$ ; $V_{DD} \leq 200\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; starting $T_j = 25\text{ °C}$ | -                                  | 210      | mJ   |
| $E_{DS(AL)R}$               | repetitive drain-source avalanche energy     | unclamped inductive load; $I_D = 1.1\text{ A}$ ; $t_p = 0.014\text{ ms}$ ; $V_{DD} \leq 200\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$                               | <sup>[1]</sup> -<br><sup>[2]</sup> | 2.1      | mJ   |

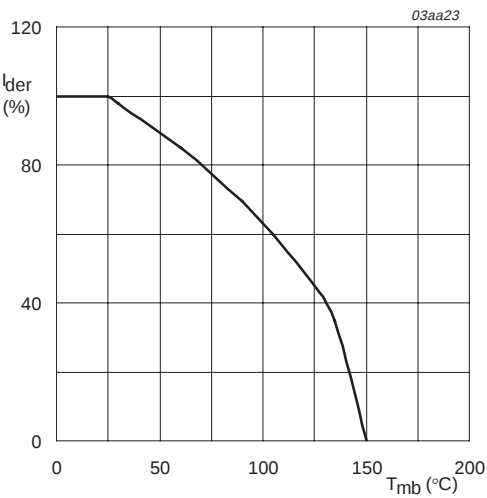
[1] Duty cycle limited by maximum junction temperature.

[2] Repetitive avalanche failure is not determined simply by thermal effects. Repetitive avalanche transients should only be applied for short bursts, not every switching cycle.



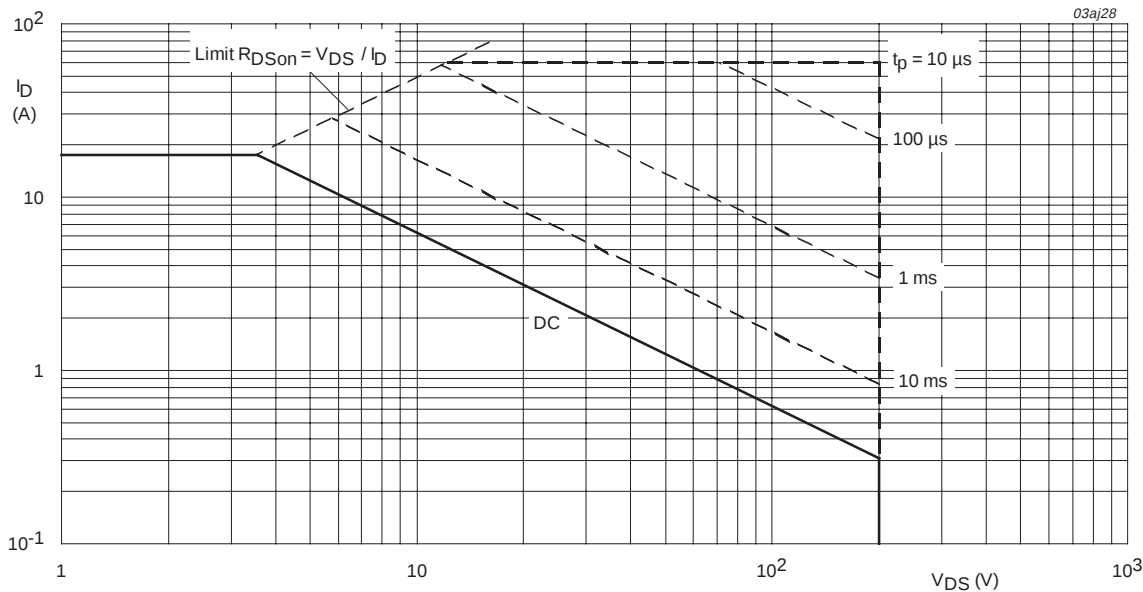
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature.



$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is single pulse;  $V_{GS} = 10 V$

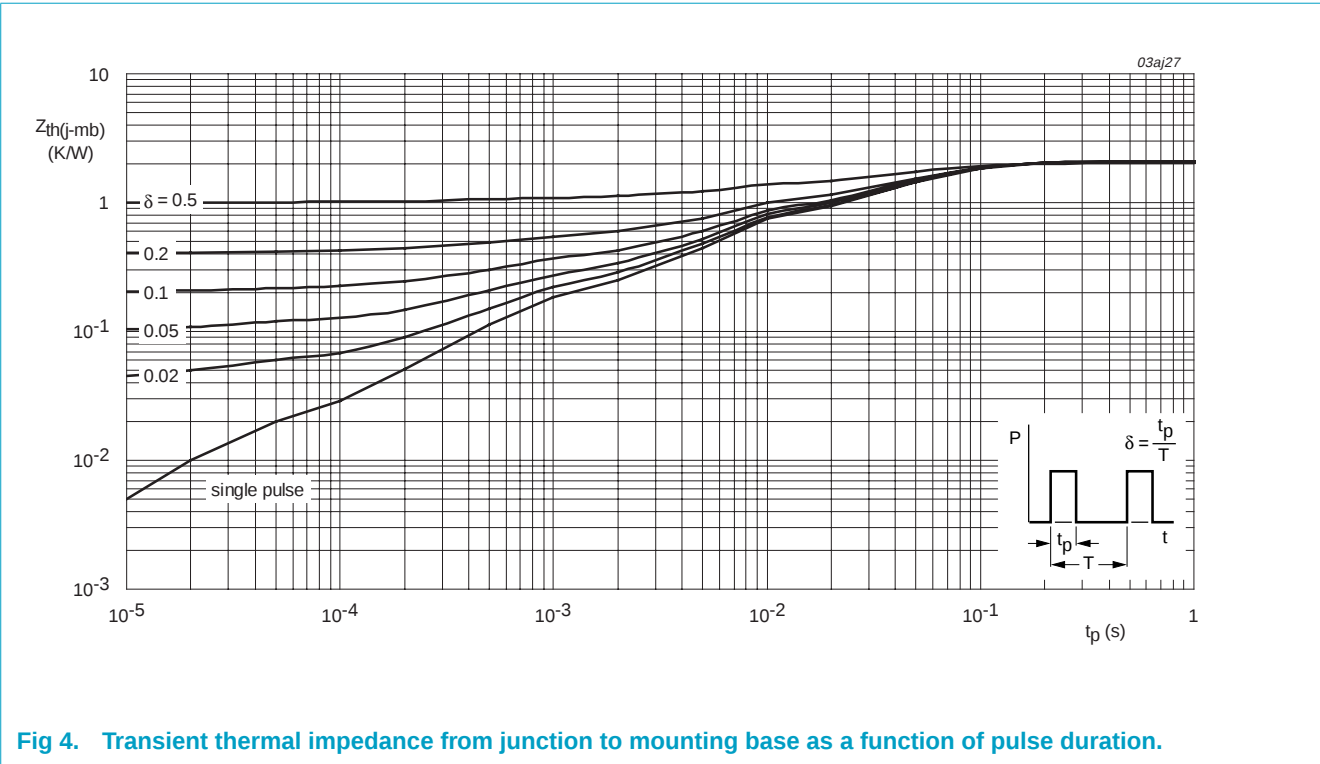
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 4: Thermal characteristics

| Symbol         | Parameter                                         | Conditions | Min | Typ | Max | Unit |
|----------------|---------------------------------------------------|------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | Figure 4   | -   | -   | 2   | K/W  |

5.1 Transient thermal impedance

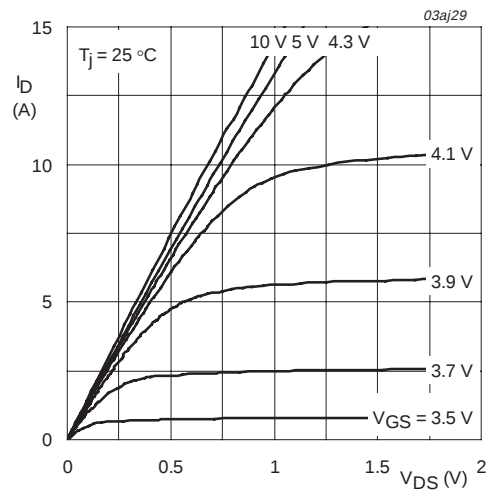


## 6. Characteristics

**Table 5: Characteristics**

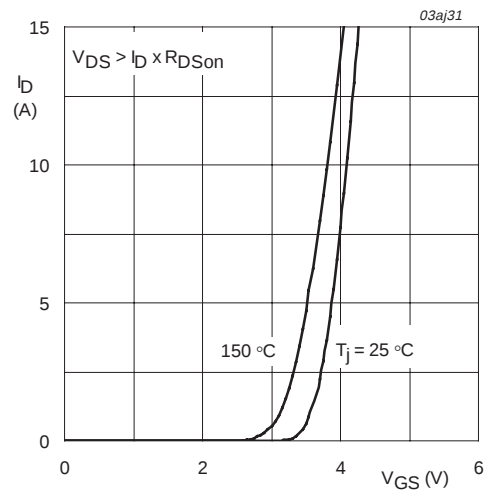
$T_j = 25\text{ °C}$  unless otherwise specified.

| Symbol                         | Parameter                            | Conditions                                                                               | Min | Typ  | Max | Unit          |
|--------------------------------|--------------------------------------|------------------------------------------------------------------------------------------|-----|------|-----|---------------|
| <b>Static characteristics</b>  |                                      |                                                                                          |     |      |     |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage       | $I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$                                   |     |      |     |               |
|                                |                                      | $T_j = 25\text{ °C}$                                                                     | 200 | -    | -   | V             |
|                                |                                      | $T_j = -55\text{ °C}$                                                                    | 178 | -    | -   | V             |
| $V_{GS(th)}$                   | gate-source threshold voltage        | $I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; <b>Figure 9</b>                                |     |      |     |               |
|                                |                                      | $T_j = 25\text{ °C}$                                                                     | 2   | 3    | 4   | V             |
|                                |                                      | $T_j = 150\text{ °C}$                                                                    | 1.2 | -    | -   | V             |
|                                |                                      | $T_j = -55\text{ °C}$                                                                    | -   | -    | 4.4 | V             |
| $I_{DSS}$                      | drain-source leakage current         | $V_{DS} = 160\text{ V}$ ; $V_{GS} = 0\text{ V}$                                          |     |      |     |               |
|                                |                                      | $T_j = 25\text{ °C}$                                                                     | -   | -    | 1   | $\mu\text{A}$ |
|                                |                                      | $T_j = 150\text{ °C}$                                                                    | -   | -    | 100 | $\mu\text{A}$ |
| $I_{GSS}$                      | gate-source leakage current          | $V_{GS} = \pm 20\text{ V}$ ; $V_{DS} = 0\text{ V}$                                       | -   | 10   | 100 | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance     | $V_{GS} = 10\text{ V}$ ; $I_D = 15\text{ A}$ ; <b>Figure 7 and 8</b>                     |     |      |     |               |
|                                |                                      | $T_j = 25\text{ °C}$                                                                     | -   | 71   | 85  | m $\Omega$    |
|                                |                                      | $T_j = 150\text{ °C}$                                                                    | -   | 170  | 204 | m $\Omega$    |
|                                |                                      | $V_{GS} = 10\text{ V}$ ; $I_D = 3\text{ A}$ ; <b>Figure 7 and 8</b>                      | -   | 68   | 80  | m $\Omega$    |
| <b>Dynamic characteristics</b> |                                      |                                                                                          |     |      |     |               |
| $Q_{g(tot)}$                   | total gate charge                    | $I_D = 4\text{ A}$ ; $V_{DD} = 100\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <b>Figure 13</b> | -   | 40   | -   | nC            |
| $Q_{gs}$                       | gate-source charge                   |                                                                                          | -   | 6    | -   | nC            |
| $Q_{gd}$                       | gate-drain (Miller) charge           |                                                                                          | -   | 12.7 | -   | nC            |
| $C_{iss}$                      | input capacitance                    | $V_{GS} = 0\text{ V}$ ; $V_{DS} = 30\text{ V}$ ; $f = 1\text{ MHz}$ ; <b>Figure 11</b>   | -   | 2170 | -   | pF            |
| $C_{oss}$                      | output capacitance                   |                                                                                          | -   | 220  | -   | pF            |
| $C_{rss}$                      | reverse transfer capacitance         |                                                                                          | -   | 70   | -   | pF            |
| $t_{d(on)}$                    | turn-on delay time                   | $V_{DD} = 100\text{ V}$ ; $R_L = 100\text{ }\Omega$ ;                                    | -   | 21   | -   | ns            |
| $t_r$                          | rise time                            | $V_{GS} = 10\text{ V}$ ; $R_G = 5.6\text{ }\Omega$                                       | -   | 12   | -   | ns            |
| $t_{d(off)}$                   | turn-off delay time                  |                                                                                          | -   | 58   | -   | ns            |
| $t_f$                          | fall time                            |                                                                                          | -   | 38   | -   | ns            |
| <b>Source-drain diode</b>      |                                      |                                                                                          |     |      |     |               |
| $V_{SD}$                       | source-drain (diode forward) voltage | $I_S = 10\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; <b>Figure 12</b>                           | -   | 0.86 | 1.2 | V             |
| $t_{rr}$                       | reverse recovery time                | $I_S = 10\text{ A}$ ; $dI_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$      | -   | 190  | -   | ns            |
| $Q_r$                          | recovered charge                     |                                                                                          | -   | 355  | -   | nC            |



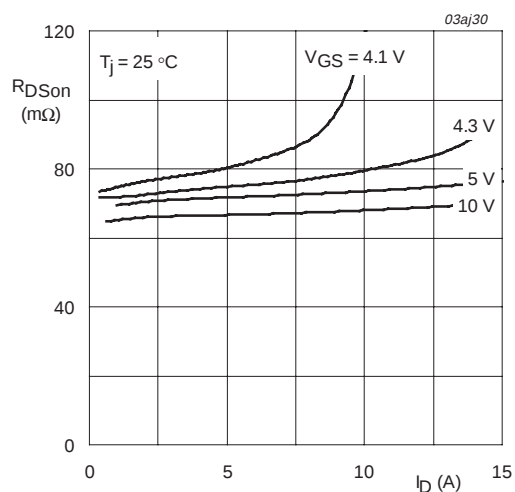
$T_j = 25\text{ }^{\circ}\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



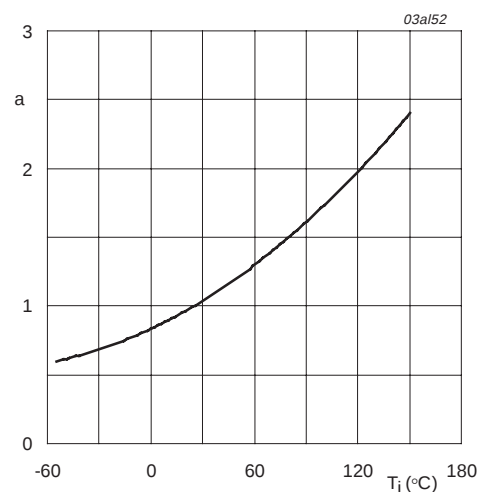
$T_j = 25\text{ }^{\circ}\text{C}$  and  $150\text{ }^{\circ}\text{C}$ ;  $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



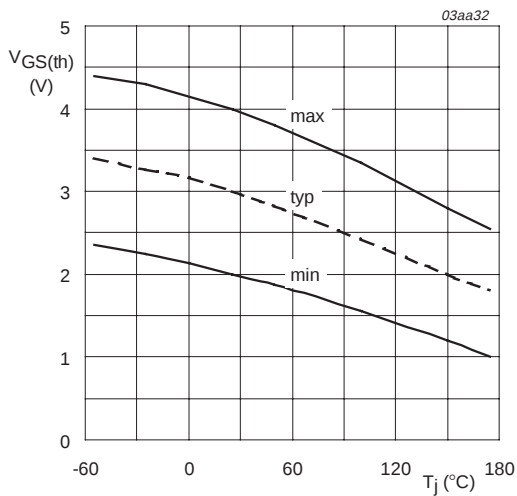
$T_j = 25\text{ }^{\circ}\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



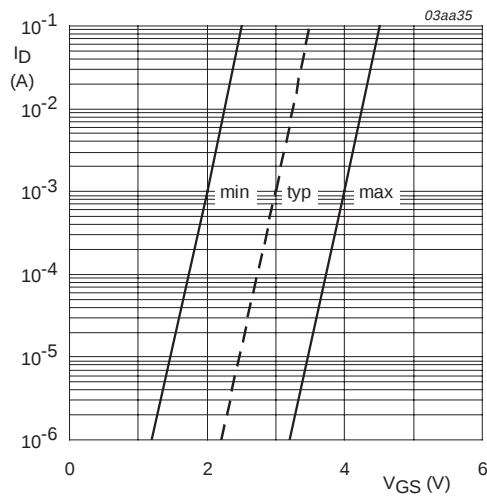
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



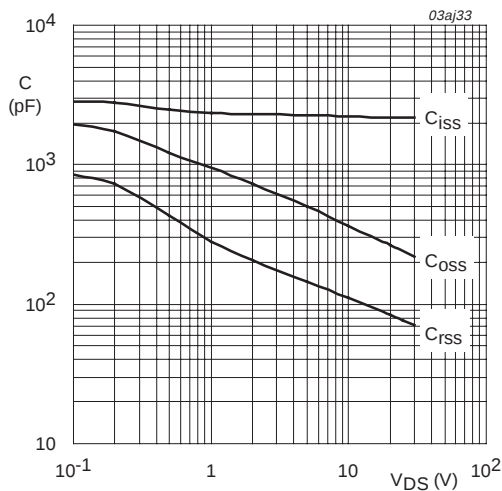
$I_D = 1 \text{ mA}$ ;  $V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



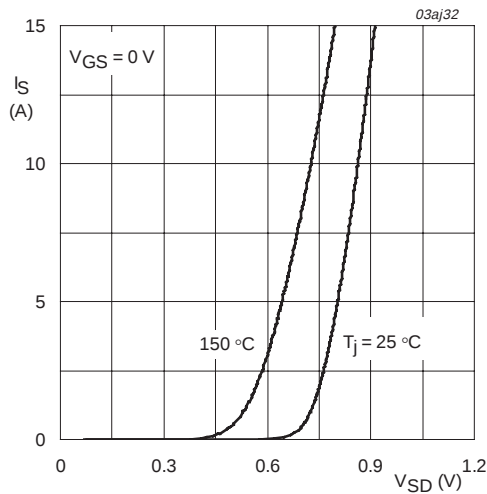
$T_j = 25 \text{ }^{\circ}C$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



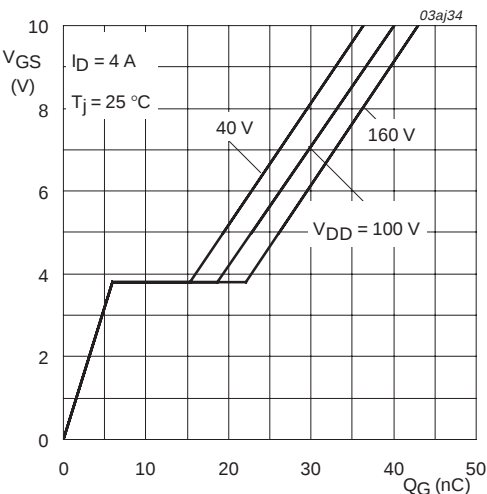
$V_{GS} = 0 \text{ V}$ ;  $f = 1 \text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25\text{ °C}$  and  $150\text{ °C}$ ;  $V_{GS} = 0\text{ V}$

Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 4\text{ A}$ ;  $V_{DD} = 40\text{ V}$ ,  $100\text{ V}$ ,  $160\text{ V}$

Fig 13. Gate-source voltage as a function of gate charge; typical values.

7. Package outline

HVSON8: plastic thermal enhanced very thin small outline package; no leads;  
8 terminals; body 6 x 5 x 0.85 mm

SOT685-1

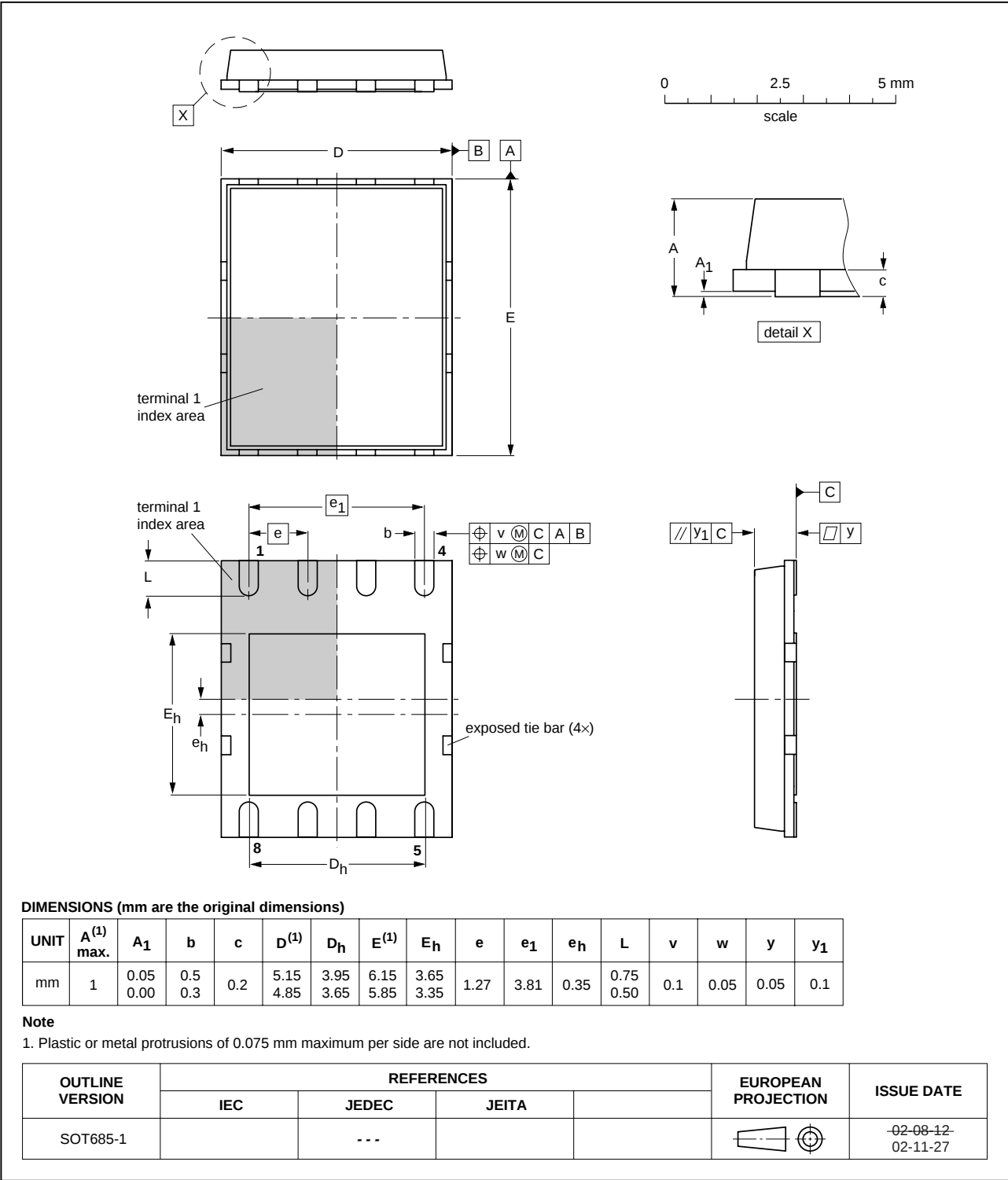
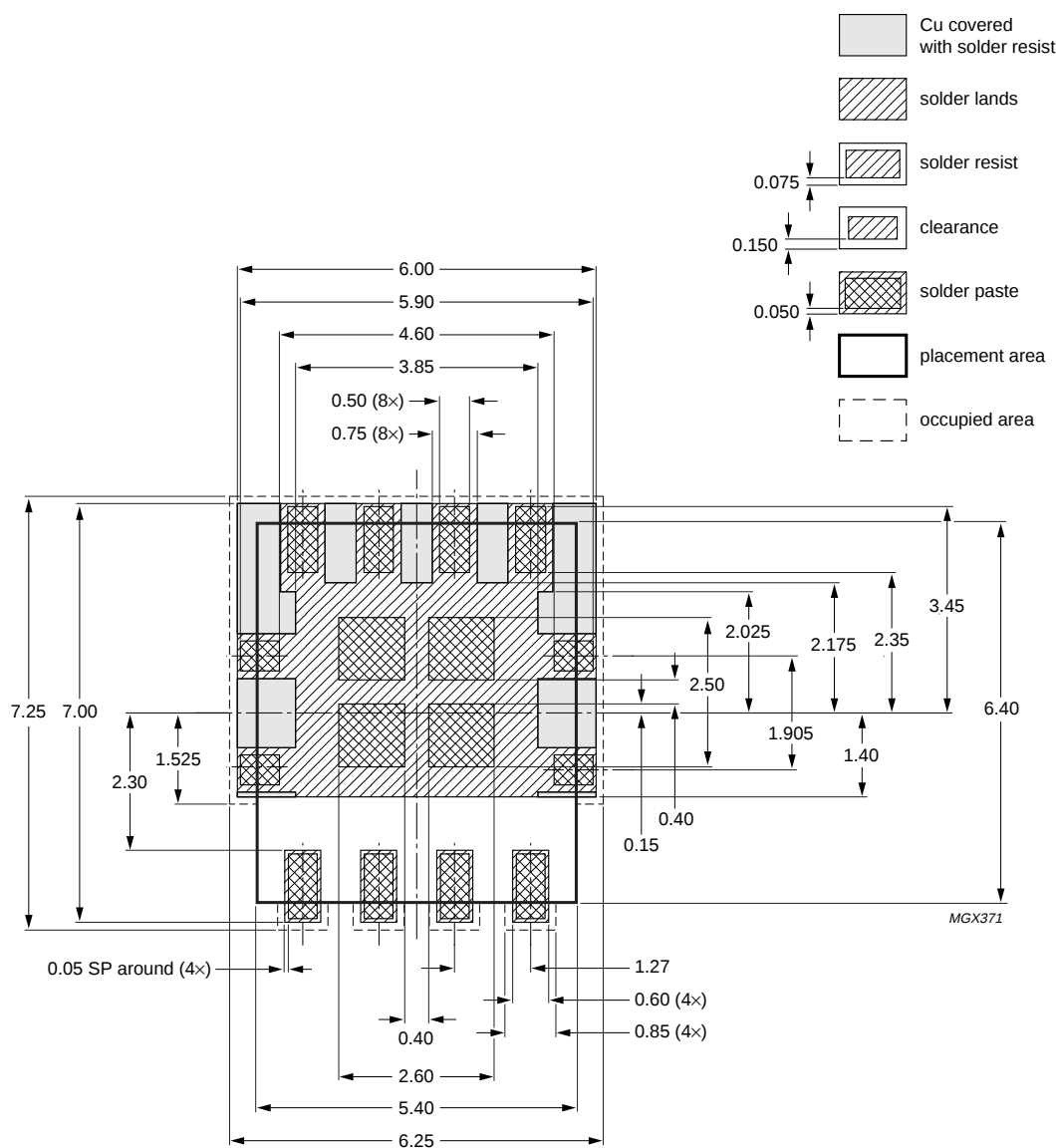


Fig 14. SOT685-1 (QLPAK)

## 8. Soldering



Dimensions in mm.

**Fig 15. Reflow soldering footprint for SOT685-1 (QLPAK).**

## 9. Revision history

Table 6: Revision history

| Rev | Date     | CPCN | Description                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                           |
|-----|----------|------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 03  | 20030911 | -    | <b>Product data (9397 750 11845)</b><br>Modifications: <ul style="list-style-type: none"> <li>• <b>Section 3 “Ordering information”</b> Addition of ordering information.</li> <li>• <b>Section 4 “Limiting values”</b> Addition of <math>E_{DS(AL)S}</math>.</li> <li>• <b>Section 4 “Limiting values”</b> Addition of <math>E_{DS(AL)R}</math>.</li> <li>• <b>Section 6 “Characteristics” Figure 13</b> Addition of 40 V and 160 V curves.</li> <li>• <b>Section 8 “Soldering”</b> Addition of soldering footprint.</li> </ul>                                                                                                                                      |
| 02  | 20030130 | -    | <b>Preliminary data (9397 750 10881)</b><br>Modifications: <ul style="list-style-type: none"> <li>• <b>Section 5 “Thermal characteristics”</b> Thermal resistance modified.</li> <li>• <b>Section 5 “Thermal characteristics” Figure 4</b> modified.</li> <li>• <b>Section 4 “Limiting values”</b> Drain current (DC) modified.</li> <li>• <b>Section 4 “Limiting values” Figure 3</b> modified.</li> <li>• <b>Section 6 “Characteristics”</b> <math>R_{DSon}</math> <math>T_j = 150\text{ °C}</math> modified.</li> <li>• <b>Section 6 “Characteristics” Figure 8</b> modified.</li> <li>• <b>Section 7 “Package outline”</b> Mounting base repositioned.</li> </ul> |
| 01  | 20020530 | -    | <b>Preliminary data (9397 750 09868); initial version.</b>                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                            |

## 10. Data sheet status

| Level | Data sheet status <sup>[1]</sup> | Product status <sup>[2][3]</sup> | Definition                                                                                                                                                                                                                                                                                     |
|-------|----------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| I     | Objective data                   | Development                      | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.                                                                                                    |
| II    | Preliminary data                 | Qualification                    | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.             |
| III   | Product data                     | Production                       | This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). |

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

## 11. Definitions

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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For sales office addresses, send e-mail to: [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com).

Fax: +31 40 27 24825

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